

isc Silicon NPN Power Transistors

2SC2690/A

DESCRIPTION

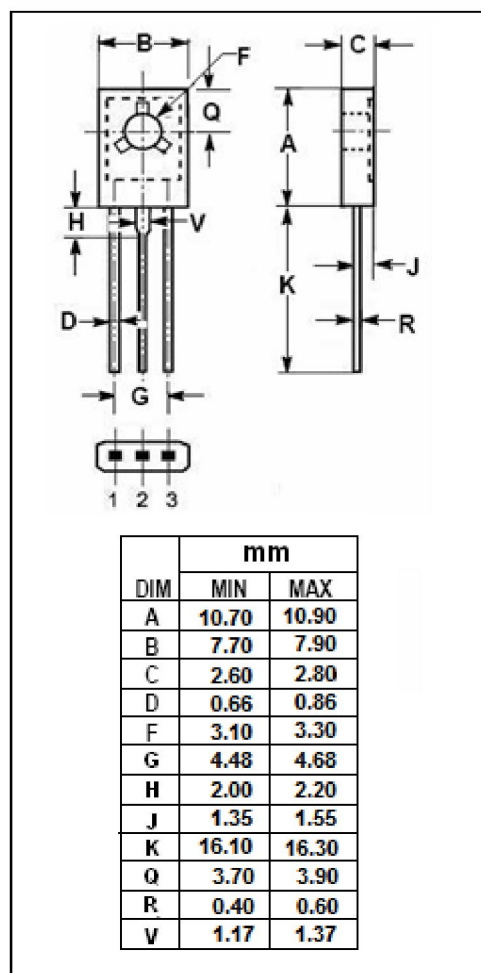
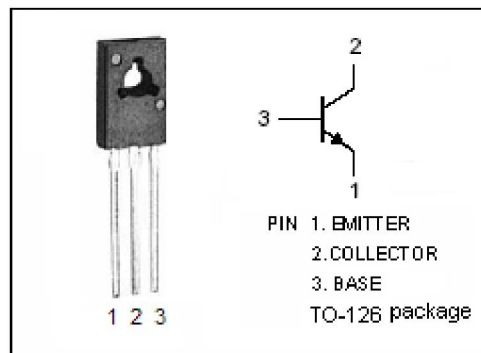
- Good Linearity of h_{FE}
- High Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 120V(\text{Min})$ -2SC2690
= 160V(Min)-2SC2690A
- Complement to Type 2SA1220/A

APPLICATIONS

- Audio frequency power amplifier
- High frequency power amplifier

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER		VALUE	UNIT
V_{CBO}	Collector-Base Voltage	2SC2690	120	V
		2SC2690A	160	
V_{CEO}	Collector-Emitter Voltage	2SC2690	120	V
		2SC2690A	160	
V_{EBO}	Emitter-Base Voltage		5	V
I_C	Collector Current-Continuous		1.2	A
I_{CM}	Collector Current-Peak		2.5	A
I_B	Base Current-Continuous		0.3	A
P_C	Collector Power Dissipation @ $T_a=25^{\circ}\text{C}$		1.2	W
	Total Power Dissipation @ $T_C=25^{\circ}\text{C}$		20	
T_J	Junction Temperature		150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range		-55~150	$^{\circ}\text{C}$



isc Silicon NPN Power Transistors**2SC2690/A****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 1A; I _B = 0.2A			0.7	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 1A; I _B = 0.2A			1.3	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 120V; I _E = 0			1.0	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = 3V; I _C =0			1.0	μ A
h _{FE-1}	DC Current Gain	I _C = 5mA ; V _{CE} = 5V	35			
h _{FE-2}	DC Current Gain	I _C = 0.3A ; V _{CE} = 5V	60		320	
f _T	Current-Gain—Bandwidth Product	I _C = 0.2A ; V _{CE} = 5V		155		MHz
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = 10V; f _{test} = 1.0MHz		19		pF

◆ h_{FE-2} Classifications

R	Q	P
60-120	100-200	160-320